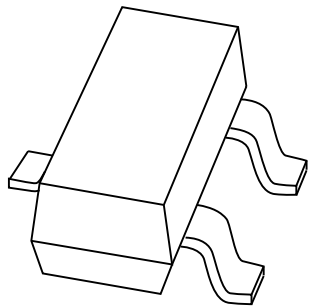


# DATA SHEET



## **PMBT2907; PMBT2907A** PNP switching transistors

Product data sheet  
Supersedes data of 1999 Apr 27

2004 Jan 16

# PNP switching transistors

# PMBT2907; PMBT2907A

### FEATURES

- High current (max. 600 mA)
- Low voltage (max. 60 V).

### APPLICATIONS

- Switching and linear amplification.

### DESCRIPTION

PNP switching transistor in a SOT23 plastic package.  
NPN complements: PMBT2222 and PMBT2222A.

### MARKING

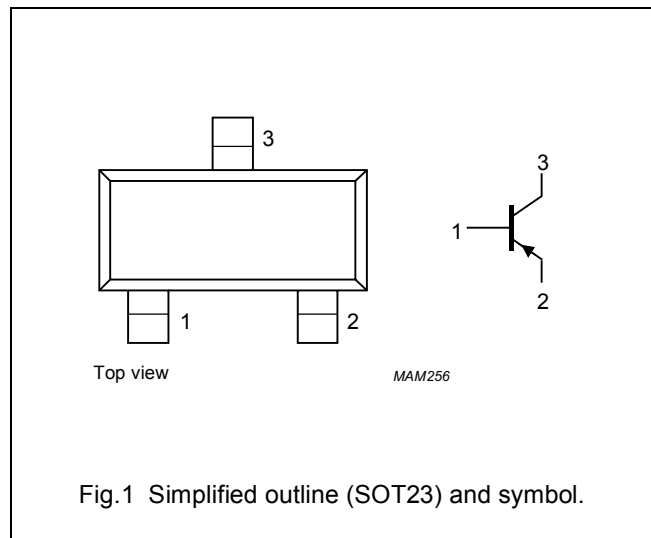
TYPE NUMBER	MARKING CODE <sup>(1)</sup>
PMBT2907	*2B
PMBT2907A	*2F

### Note

- \* = p : Made in Hong Kong.  
\* = t : Made in Malaysia.  
\* = W: Made in China.

### PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



### ORDERING INFORMATION

TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
PMBT2907	–	plastic surface mounted package; 3 leads	SOT23
PMBT2907A	–	plastic surface mounted package; 3 leads	SOT23

## PNP switching transistors

## PMBT2907; PMBT2907A

**LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{CBO}$	collector-base voltage	open emitter	–	–60	V
$V_{CEO}$	collector-emitter voltage	open base	–	–40	V
	PMBT2907 PMBT2907A		–	–60	V
$V_{EBO}$	emitter-base voltage	open collector	–	–5	V
$I_C$	collector current (DC)		–	–600	mA
$I_{CM}$	peak collector current		–	–800	mA
$I_{BM}$	peak base current		–	–200	mA
$P_{tot}$	total power dissipation	$T_{amb} \leq 25\text{ °C}$	–	250	mW
$T_{stg}$	storage temperature		–65	+150	°C
$T_j$	junction temperature		–	150	°C
$T_{amb}$	operating ambient temperature		–65	+150	°C

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th(j-a)}$	thermal resistance from junction to ambient	note 1	500	K/W

**Note**

1. Transistor mounted on an FR4 printed-circuit board.

## PNP switching transistors

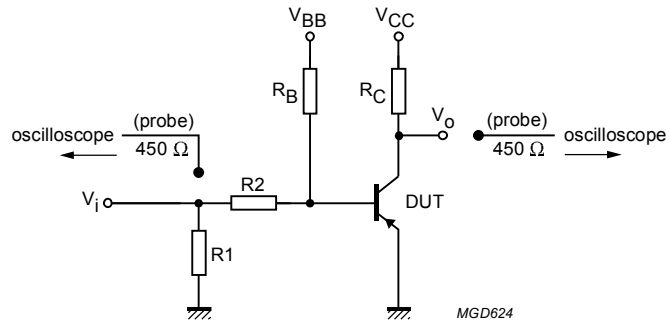
## PMBT2907; PMBT2907A

**CHARACTERISTICS**T<sub>j</sub> = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I <sub>CBO</sub>	collector-base cut-off current PMBT2907	I <sub>E</sub> = 0; V <sub>CB</sub> = -50 V	-	-20	nA
	PMBT2907A		-	-10	nA
	collector-base cut-off current PMBT2907	I <sub>E</sub> = 0; V <sub>CB</sub> = -50 V; T <sub>j</sub> = 125 °C	-	-20	μA
	PMBT2907A		-	-10	μA
I <sub>EBO</sub>	emitter-base cut-off current	I <sub>C</sub> = 0; V <sub>EB</sub> = -5 V	-	-50	nA
h <sub>FE</sub>	DC current gain PMBT2907	I <sub>C</sub> = -0.1 mA; V <sub>CE</sub> = -10 V	35	-	
	PMBT2907A		75	-	
	DC current gain PMBT2907	I <sub>C</sub> = -1 mA; V <sub>CE</sub> = -10 V	50	-	
	PMBT2907A		100	-	
	DC current gain PMBT2907	I <sub>C</sub> = -10 mA; V <sub>CE</sub> = -10 V	75	-	
	PMBT2907A		100	-	
DC current gain PMBT2907	I <sub>C</sub> = -150 mA; V <sub>CE</sub> = -10 V	100	300		
DC current gain PMBT2907	I <sub>C</sub> = -500 mA; V <sub>CE</sub> = -10 V	30	-		
PMBT2907A		50	-		
V <sub>CEsat</sub>	collector-emitter saturation voltage	I <sub>C</sub> = -150 mA; I <sub>B</sub> = -15 mA	-	-400	mV
		I <sub>C</sub> = -500 mA; I <sub>B</sub> = -50 mA	-	-1.6	V
V <sub>BEsat</sub>	base-emitter saturation voltage	I <sub>C</sub> = -150 mA; I <sub>B</sub> = -15 mA	-	-1.3	V
		I <sub>C</sub> = -500 mA; I <sub>B</sub> = -50 mA	-	-2.6	V
C <sub>c</sub>	collector capacitance	I <sub>E</sub> = I <sub>e</sub> = 0; V <sub>CB</sub> = -10 V; f = 1 MHz	-	8	pF
C <sub>e</sub>	emitter capacitance	I <sub>C</sub> = I <sub>c</sub> = 0; V <sub>EB</sub> = -2 V; f = 1 MHz	-	30	pF
f <sub>T</sub>	transition frequency	I <sub>C</sub> = -50 mA; V <sub>CE</sub> = -20 V; f = 100 MHz	200	-	MHz
<b>Switching times (between 10% and 90% levels); (see Fig.2)</b>					
t <sub>on</sub>	turn-on time	I <sub>Con</sub> = -150 mA; I <sub>Bon</sub> = -15 mA; I <sub>Boff</sub> = 15 mA	-	40	ns
t <sub>d</sub>	delay time		-	12	ns
t <sub>r</sub>	rise time		-	30	ns
t <sub>off</sub>	turn-off time		-	365	ns
t <sub>s</sub>	storage time		-	300	ns
t <sub>f</sub>	fall time		-	65	ns

## PNP switching transistors

## PMBT2907; PMBT2907A



$V_i = -9.5 \text{ V}$ ;  $T = 500 \mu\text{s}$ ;  $t_p = 10 \mu\text{s}$ ;  $t_r = t_f \leq 3 \text{ ns}$ .  
 $R_1 = 68 \Omega$ ;  $R_2 = 325 \Omega$ ;  $R_B = 325 \Omega$ ;  $R_C = 160 \Omega$ .  
 $V_{BB} = 3.5 \text{ V}$ ;  $V_{CC} = -29.5 \text{ V}$ .  
Oscilloscope: input impedance  $Z_i = 50 \Omega$ .

Fig.2 Test circuit for switching times.

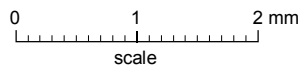
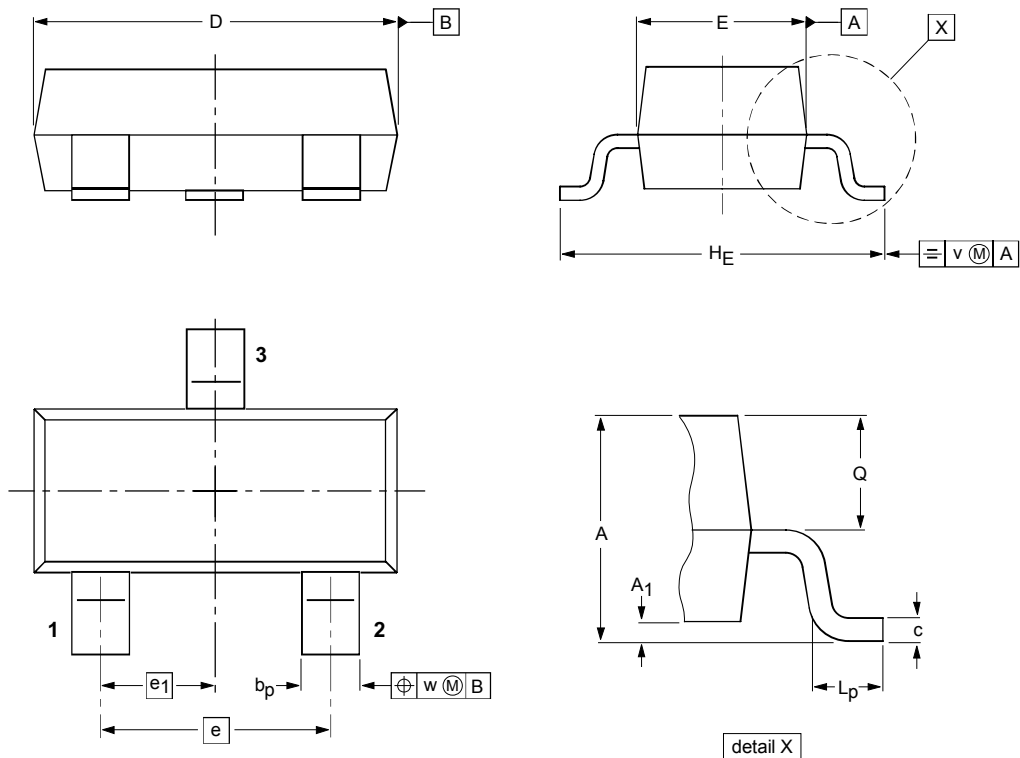
PNP switching transistors

PMBT2907; PMBT2907A

PACKAGE OUTLINE

Plastic surface-mounted package; 3 leads

SOT23



DIMENSIONS (mm are the original dimensions)

UNIT	A	A <sub>1</sub> max.	b <sub>p</sub>	c	D	E	e	e <sub>1</sub>	H <sub>E</sub>	L <sub>p</sub>	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT23		TO-236AB				04-11-04 06-03-16

PNP switching transistors

PMBT2907; PMBT2907A

DATA SHEET STATUS

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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## **Customer notification**

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

## **Contact information**

For additional information please visit: <http://www.nxp.com>

For sales offices addresses send e-mail to: [salesaddresses@nxp.com](mailto:salesaddresses@nxp.com)

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